

```
> restart;
```

Suggested Solution problem 1400-2, FYS3410/9310

Problem text:

Starting with equation 14.1,

```
> eq14_1a:=F=hg*(Cg-Cs);eq14_1b:=F=ks*Cs;
```

$$eq14_1a := F = hg (Cg - Cs)$$

$$eq14_1b := F = ks Cs$$

(1)

derive equation 14.2.

```
> eq14_2:=R = ks*hg*Cg/(N*(ks+hg));
```

$$eq14_2 := R = \frac{ks \, hg \, Cg}{N (ks + hg)}$$

(2)

SOLUTION

Straight forward

We write the growth rate R from the flux F (of molecules) when n is the number of Si atoms pr gas molecule and N_{Si} is the atomic density of Si xtal

```
> eq1:=R=n*F/N_Si;
```

$$eq1 := R = \frac{n F}{N_{Si}}$$

(3)

So, by putting equation 14_1b for the flux we have

```
> eq2a:=subs(eq14_1b,eq1);
```

$$eq2a := R = \frac{n \, ks \, Cs}{N_{Si}}$$

(4)

We now need to express Cs in terms of Cg which is the concentration we can control.

Since the definition in the book of N is $n/N_{Si}=1/N$, with we have

```
> eq3:=N_Si=n*N;
```

$$eq3 := N_{Si} = n N$$

(5)

```
> eq2:=subs(eq3,eq2a);
```

$$eq2 := R = \frac{ks \, Cs}{N}$$

(6)

```
> eq4:=Cs=solve(rhs(eq14_1a)=rhs(eq14_1b),Cs);
```

$$eq4 := Cs = \frac{hg \, Cg}{ks + hg}$$

(7)

```
> QED:=subs(eq4,eq2);
```

$$QED := R = \frac{ks \, hg \, Cg}{N (ks + hg)}$$

(8)

or equivalently skip the explicit step eq2a, include eq3 and write in on line

```
> qed:=subs(Cs=solve(rhs(eq14_1a)=rhs(eq14_1b),Cs),  
             subs(eq3,subs(eq14_1b,eq1)));
```

$$qed := R = \frac{ks \, hg \, Cg}{N (ks + hg)}$$

(9)